

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB860

Silicon PNP Triple Diffused

RENESAS

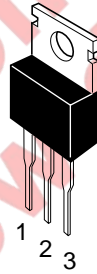
ADE-208-861 (Z)
1st. Edition
September 2000

Application

Low frequency power amplifier TV vertical deflection output complementary pair with 2SD1137

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

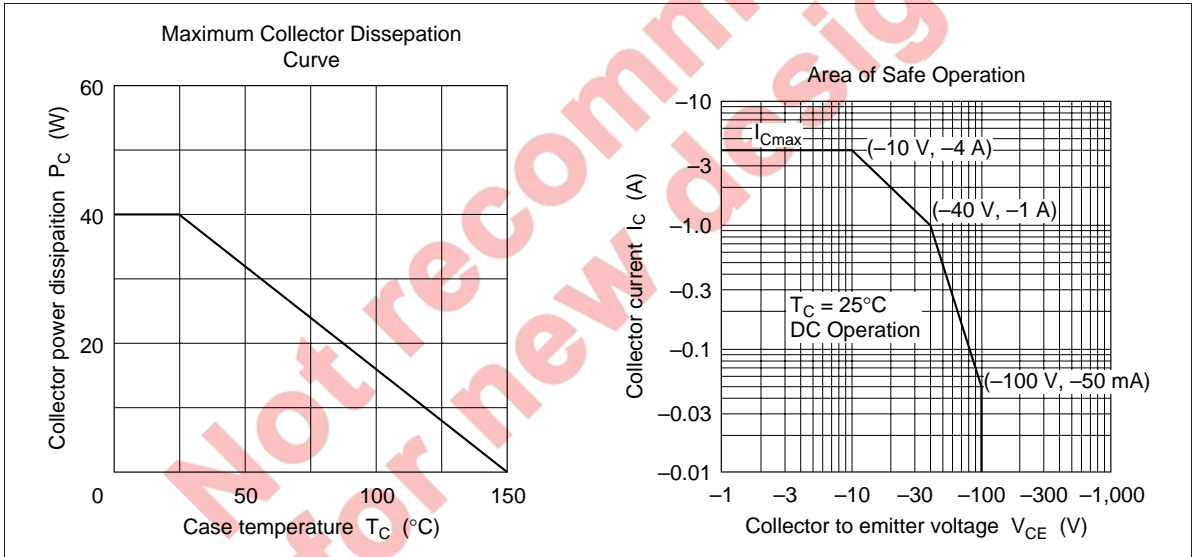
| Item | Symbol | Rating | Unit |
|------------------------------|---------------|-------------|------|
| Collector to base voltage | V_{CBO} | -100 | V |
| Collector to emitter voltage | V_{CE} | -100 | V |
| Emitter to base voltage | V_{EBO} | -4 | V |
| Collector current | I_C | -4 | A |
| Collector peak current | $I_{C(peak)}$ | -5 | A |
| Collector power dissipation | P_C | 1.8 | W |
| | P_C^{*1} | 40 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -45 to +150 | °C |

Note: 1. Value at $T_C = 25^\circ\text{C}$

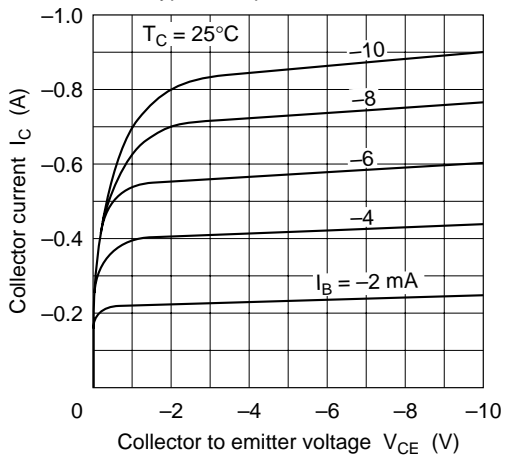
Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|---------------|------|-----|------|-------------------------|--|
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | -100 | — | — | V | $I_C = -10 \text{ mA}$, $R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | -4 | — | — | V | $I_E = -1 \text{ mA}$, $I_C = 0$ |
| Collector cutoff current | I_{CEO} | — | — | -100 | μA | $V_{CE} = -80 \text{ V}$, $R_{BE} = \infty$ |
| Emitter cutoff current | I_{EBO} | — | — | -50 | μA | $V_{EB} = -3.5 \text{ V}$, $I_C = 0$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | — | — | -1.0 | V | $I_C = -1 \text{ A}$, $I_B = -0.1 \text{ A}^{*1}$ |
| DC current transfer ratio | h_{FE} | 50 | — | 250 | $V_{CE} = -4 \text{ V}$ | $I_C = -0.5 \text{ A}^{*1}$ |
| | | 25 | — | 350 | | $I_C = -50 \text{ mA}$ |

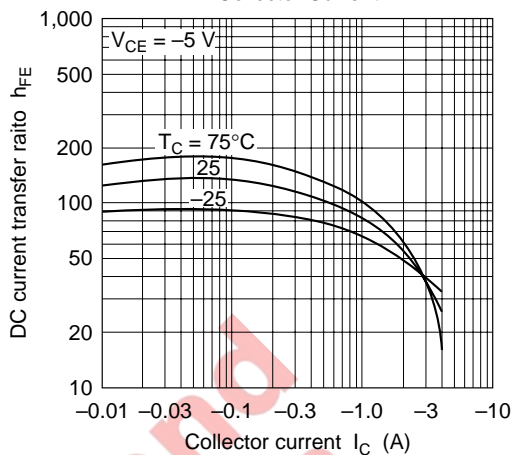
Note: 1. Pulse test



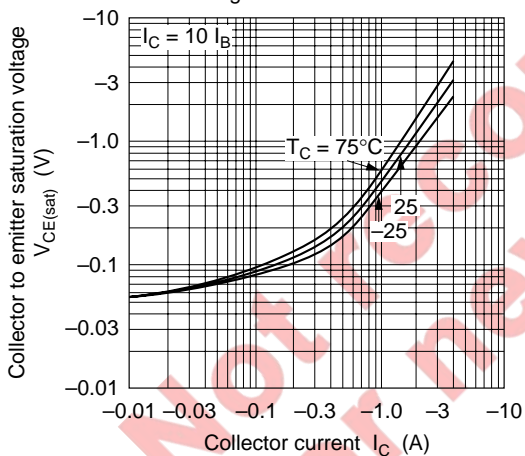
Typical Output Characteristics



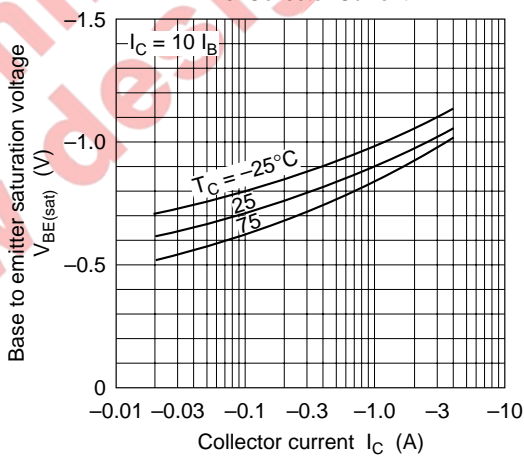
DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current



Base to Emitter Saturation Voltage vs. Collector Current



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